General Description

The SJJG015R65 uses advanced SIC technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 18V. This device is suitable for use as a wide variety of applications.

Features

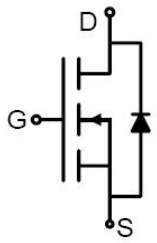
- Wide Bandgap SiC MOSFET Technology
- Low On-Resistance with High Blocking Voltage
- Low Capacitances with High-Speed Switching
- Low Reverse Recovery
- Easy to Parallel and Simple to Drive

Application

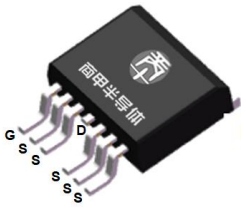
- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- Battery Chargers
- Solar Inverters

Key Performance Parametes

Parameter	Value	Unit
V_{DS}	650	V
$R_{DS(ON)\_TYP}$	15	mΩ
I_D	126	A
Q_G	146	nC



Schematic Diagram



TO-263-7L top view

RoHS

Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJJG015R65	SJJG015R65	TO-263-7L	Tape	\	\	800 Pcs

Table 1. Absolute Maximum Ratings (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage (V_{GS}=0V)	650	V
V_{GS}	Gate-Source Voltage (V_{DS}=0V)	-10/+22	V
I_D	Drain Current-Continuous(T_C=25℃)	126	A
	Drain Current-Continuous(T_C=100℃)	80	A
$I_{DM\ (pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	504	A
P_D	Maximum Power Dissipation(T_C=25℃)	368	W
	Maximum Power Dissipation(T_C=100℃)	147	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 175	℃

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		0.34	℃/W

Table 3. Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=500μA	650			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=650V, V_{GS}=0V			100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=22V, V_{DS}=0V			100	nA
		V_{GS}=-10V, V_{DS}=0V			-100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=20mA	2		4.5	V
g_{FS}	Forward Transconductance	V_{DS}=20V, I_D=60A		40.8		S
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=18V, I_D=60A		15	21	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=500V,V_{GS}=0V, f=100KHz		3525		pF
C_{oss}	Output Capacitance			297		pF
C_{rss}	Reverse Transfer Capacitance			16		pF
Rg	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		2.2		Ω
Switching Parameters						
$t_{d(on)}$	Turn-on Delay Time	V_{GS}=18V, V_{DS}=400V, R_L=6.7Ω, R_{GEN}=5.6Ω		28.8		nS
t_r	Turn-on Rise Time			25.7		nS
$t_{d(off)}$	Turn-Off Delay Time			60		nS
t_f	Turn-Off Fall Time			10.5		nS
Q_g	Total Gate Charge	V_{GS}=18V, V_{DS}=400V, I_D=60A		146		nC
Q_{gs}	Gate-Source Charge			45		nC
Q_{gd}	Gate-Drain Charge			36		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)				126	A
V_{SD}	Forward on Voltage (Note 2)	V_{GS}=0V, I_S=60A			1.2	V
t_{rr}	Reverse Recovery Time	I_F=60A, dI/dt=100A/μs		29.5		ns
Q_{rr}	Reverse Recovery Charge	I_F=60A, dI/dt=100A/μs		303		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
Notes 2.E_{AS} condition: T_J=25℃,V_{DD}=400V,V_G=18V, Rg=50Ω, L=0.5mH.
Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Electrical And Thermal Characteristics (Curves)

Figure 1. On-Region Characteristics T_J = -40℃

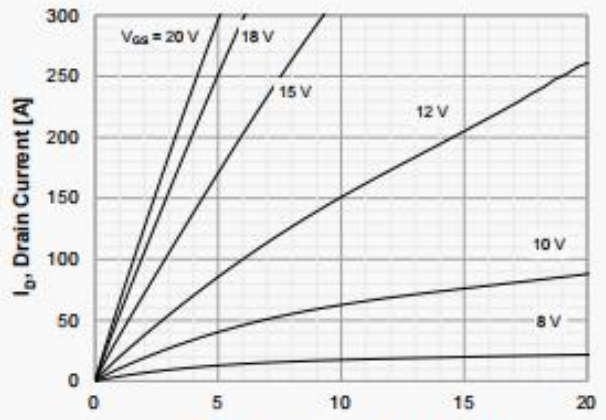


Figure 2. On-Region Characteristics T_J = 25℃

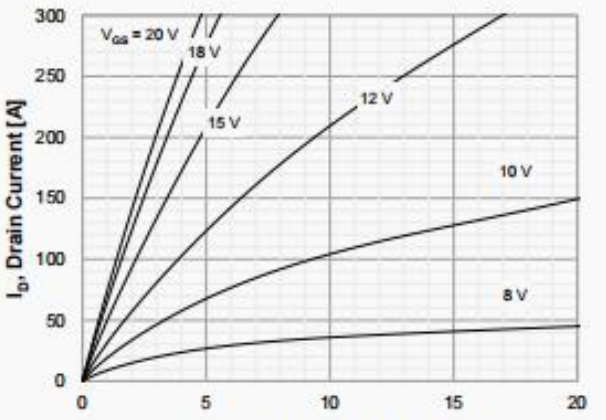


Figure 3. On-Region Characteristics T_J = 125℃

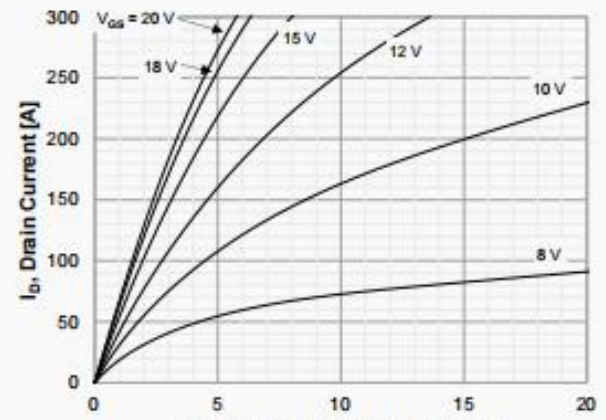


Figure 4. On-Region Characteristics T_J = 175℃

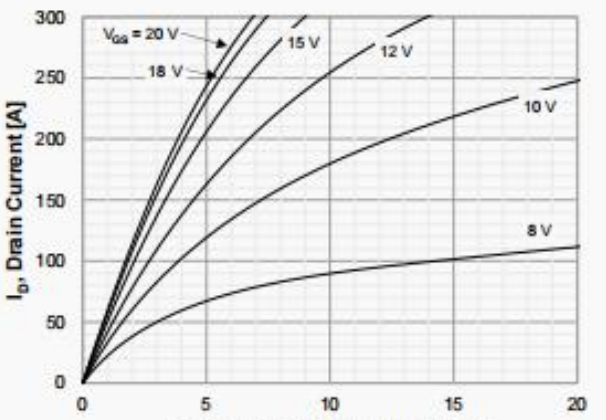


Figure 5. On-Resistance Characteristics vs. Temperature

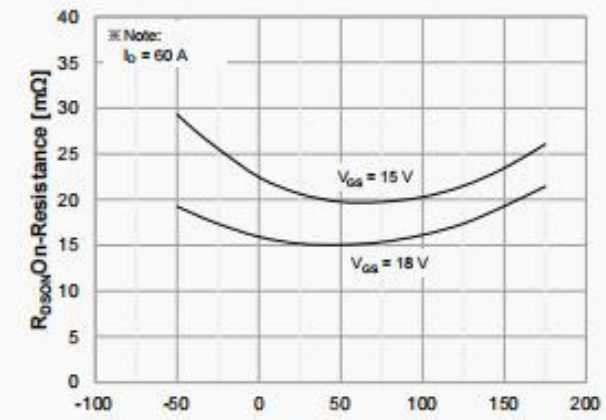
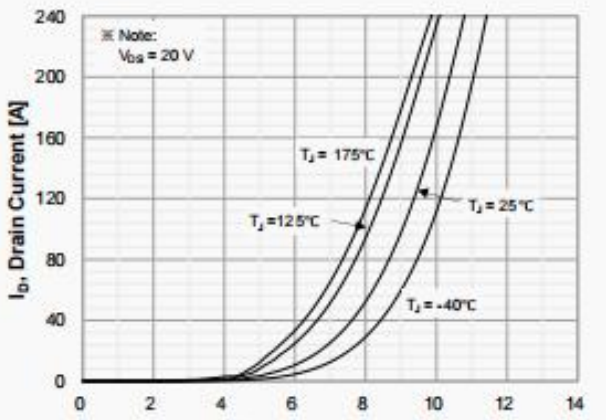


Figure 6. Transfer Characteristics



Typical Electrical And Thermal Characteristics (Curves)

Figure 7. Diode Forward Voltage Characteristics vs. Source-Drain Current T_J = -40℃

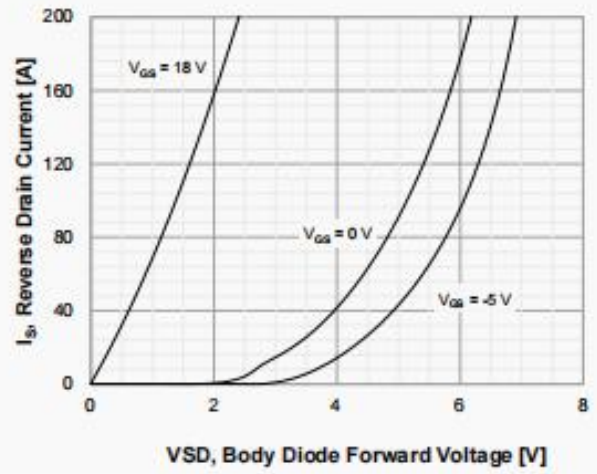


Figure 8. Diode Forward Voltage Characteristics vs. Source-Drain Current T_J = 25℃

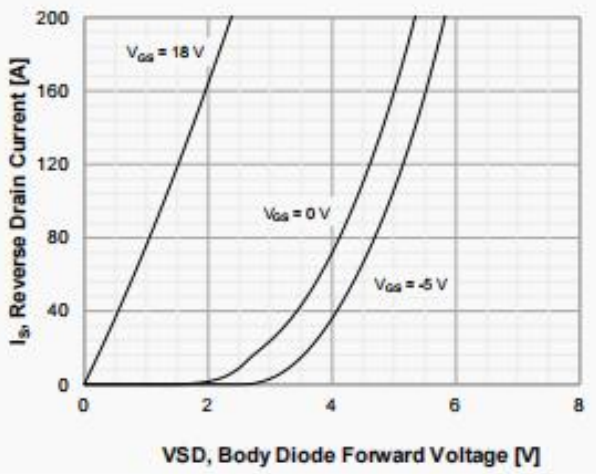


Figure 9. Diode Forward Voltage Characteristics vs. Source-Drain Current T_J = 125℃

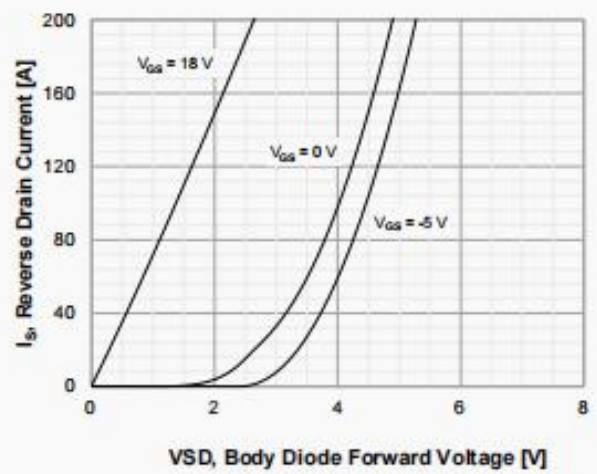


Figure 10. Diode Forward Voltage Characteristics vs. Source-Drain Current T_J = 175℃

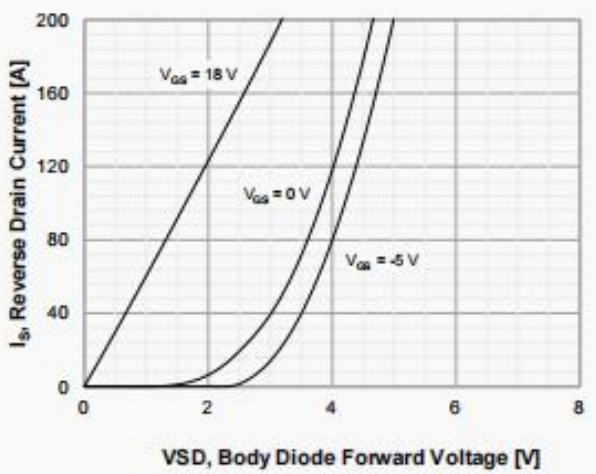


Figure 11. Threshold Voltage vs. Temperature

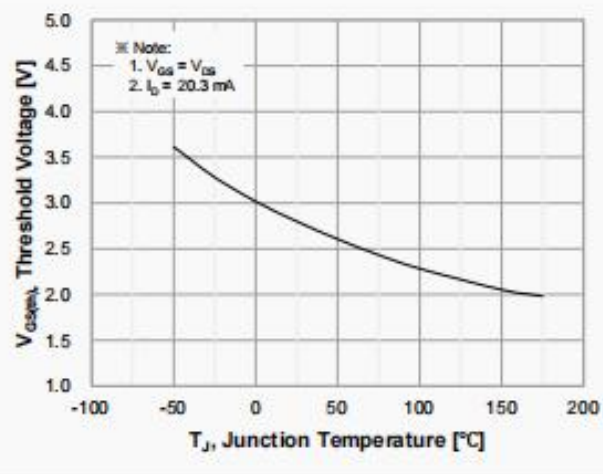
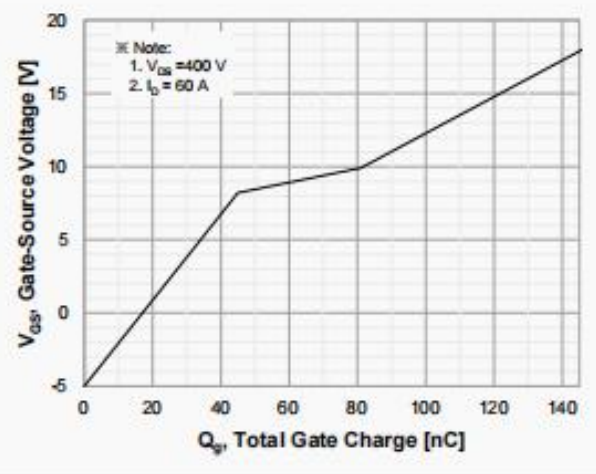


Figure 12. Gate Charge Characteristics



Typical Electrical And Thermal Characteristics (Curves)

Figure 13. Stored Energy in Output Capacitance

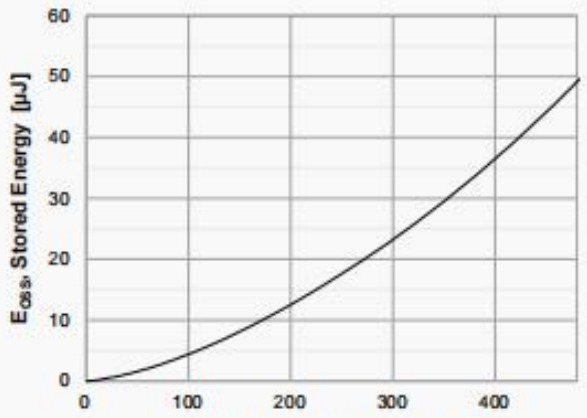


Figure 14. Capacitance Characteristics

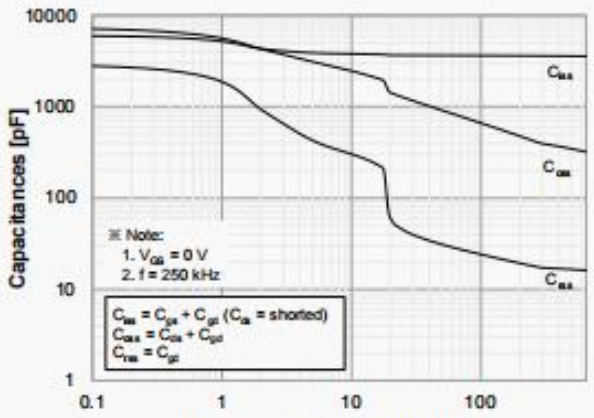


Figure 15. Continuous Drain Current Derating vs. Case Temperature

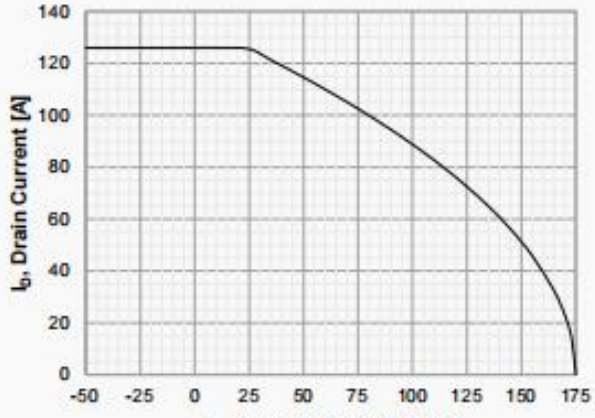


Figure 16. Maximum Power Dissipation Derating vs. Case Temperature

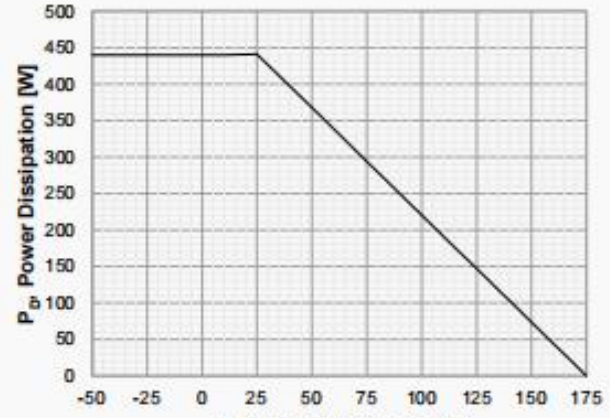


Figure 17. Typ. Switching Losses vs. Drain Current

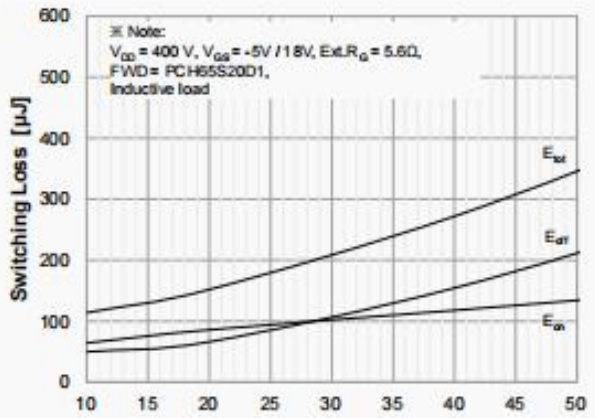
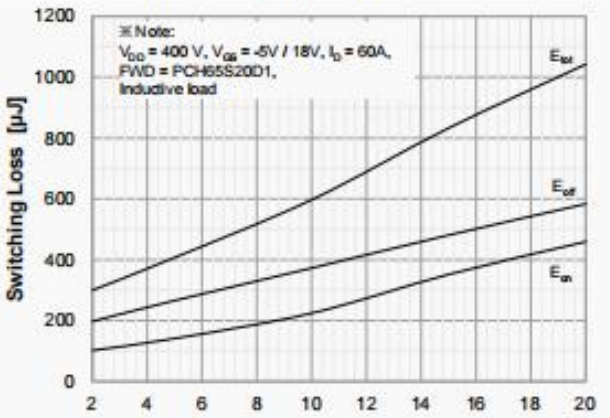


Figure 18. Typ. Switching Losses vs. Gate Resistance



Typical Electrical And Thermal Characteristics (Curves)

Figure 19. Typ. Switching Losses vs. Drain Current

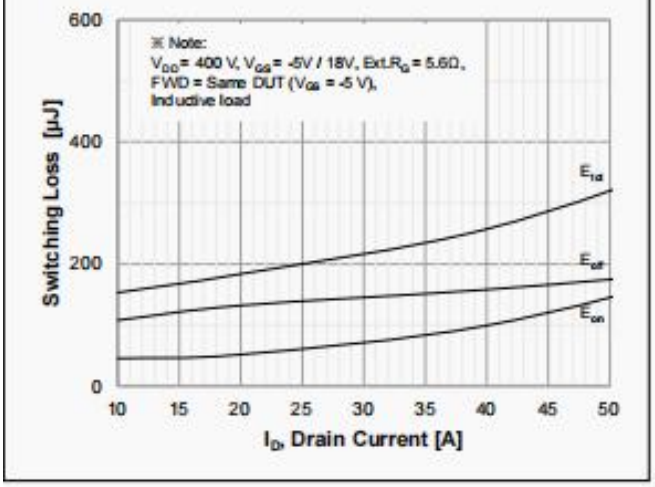


Figure 20. Typ. Switching Losses vs. Gate Resistance

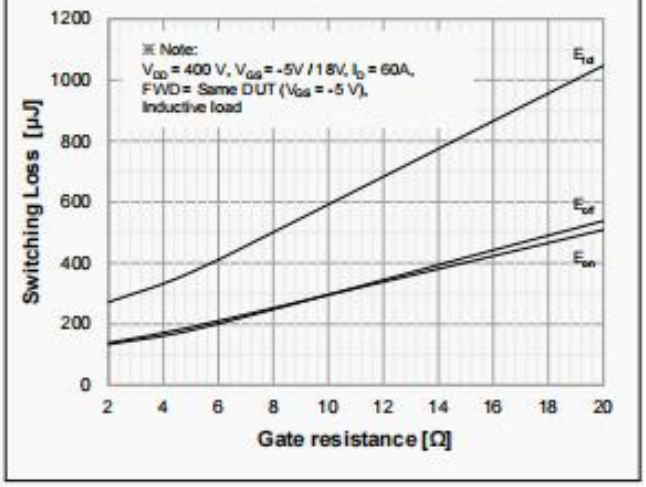


Figure 21. Maximum Safe Operating Area

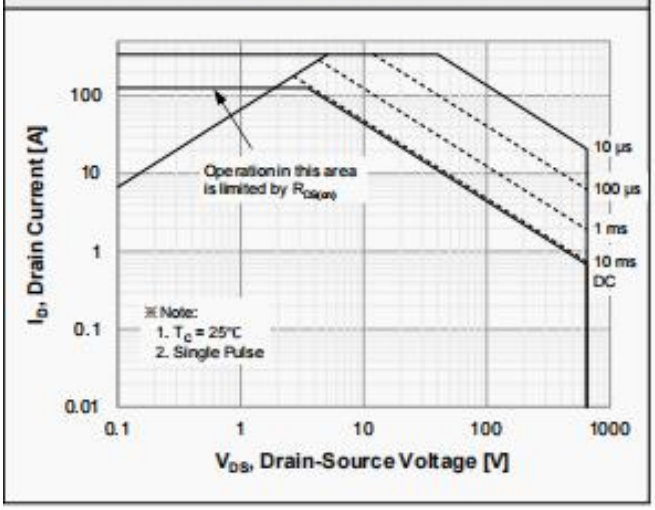
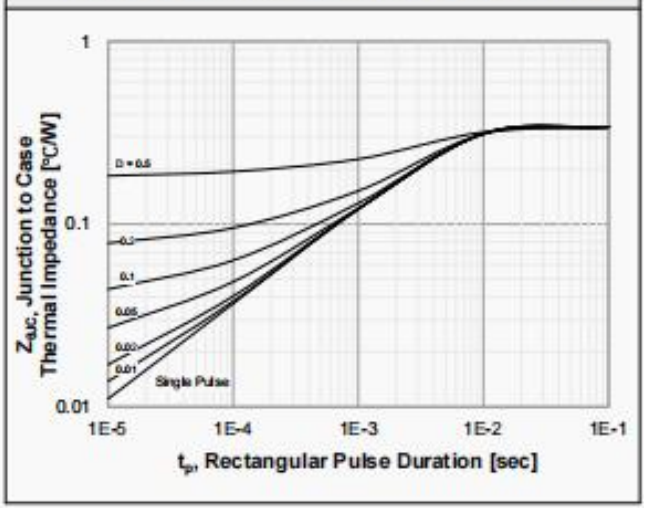
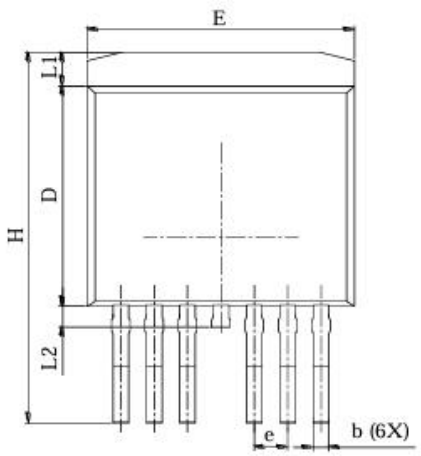


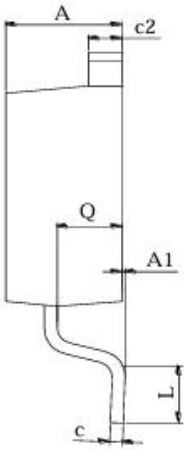
Figure 22. Transient Thermal Response Curve



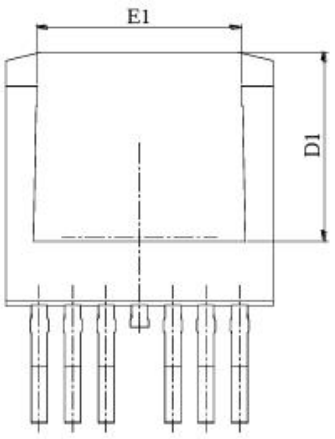
TO-263-7L Package Information



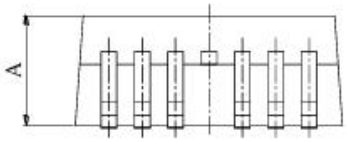
Top View



Side View



Bottom View



Front View

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.50	0.60	0.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1		7.65 REF.	
E	9.96	10.16	10.36
E1	6.80	7.80	8.00
e		1.27 BSC	
H	14.61	15.00	15.88
L	1.78	2.32	2.80
L1		1.36 REF.	
L2		1.20 REF.	
L3		0.25 BSC	
Q	2.30	2.48	2.70

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